

**Description**

The SX60P02D uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

**General Features**

$V_{DS} = -20V$   $I_D = -65A$

$R_{DS(ON)} < 8.5m\Omega$  @  $V_{GS}=4.5V$

**Application**

Battery protection

Load switch

Uninterruptible power supply

**Absolute Maximum Ratings ( $T_c=25^\circ C$  unless otherwise noted)**

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	-20	V
$V_{GS}$	Gate-Source Voltage	$\pm 12$	V
$I_D @ T_c=25^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-65	A
$I_D @ T_c=70^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-38	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	-25	A
$P_D @ T_c=25^\circ C$	Total Power Dissipation <sup>3</sup>	75	W
$P_D @ T_c=70^\circ C$	Total Power Dissipation <sup>3</sup>	55	W
$T_{STG}$	Storage Temperature Range	-55 to 150	°C
$T_J$	Operating Junction Temperature Range	-55 to 150	°C
$R_{eJA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	62.5	°C/W
$R_{eJC}$	Thermal Resistance Junction-Case <sup>1</sup>	2.0	°C/W

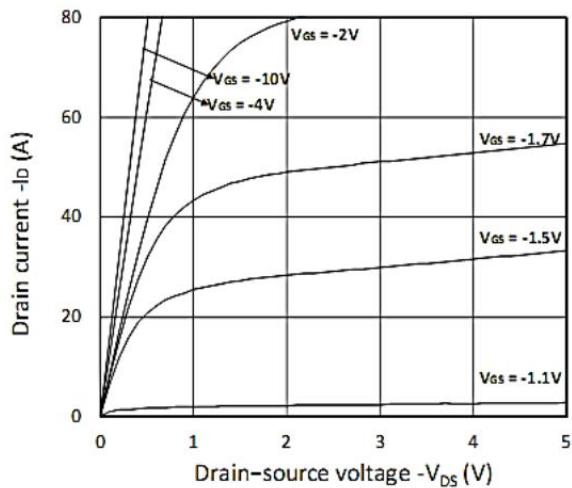
**Electrical Characteristics (T<sub>J</sub>=25°C, unless otherwise noted)**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V(BR)DSS	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA	-20	-22	-	V
I <sub>GSS</sub>	Gate-body Leakage current	V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±10V	-	-	±100	nA
IDSS	Zero Gate Voltage Drain Current T <sub>J</sub> =25°C	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V	-	-	-1	μA
	Zero Gate Voltage Drain Current T <sub>J</sub> =100°C		-	-	-100	
V <sub>GS(th)</sub>	Gate-Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA	-0.5	0.7	-1.2	V
R <sub>D(on)</sub>	Drain-Source on-Resistance <sup>4</sup>	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -20A	-	6.8	8.5	mΩ
		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -15A	-	7.5	9.0	
g <sub>fs</sub>	Forward Transconductance <sup>4</sup>	V <sub>DS</sub> = -5V, I <sub>D</sub> = -15A	-	78	-	S
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = -10V, V <sub>GS</sub> = 0V, f = 1MHz	-	3560	-	pF
C <sub>oss</sub>	Output Capacitance		-	500	-	
C <sub>rss</sub>	Reverse Transfer Capacitance		-	430	-	
R <sub>g</sub>	Gate Resistance	f = 1MHz	-	11	-	Ω
Q <sub>g</sub>	Total Gate Charge	V <sub>GS</sub> = -4.5V, V <sub>DS</sub> = -10V, I <sub>D</sub> = -15A	-	43	-	nC
Q <sub>gs</sub>	Gate-Source Charge		-	7.9	-	
Q <sub>gd</sub>	Gate-Drain Charge		-	11.2	-	
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>GS</sub> = -4.5V, V <sub>DD</sub> = -10V, R <sub>G</sub> = 3Ω, I <sub>D</sub> = -15A,	-	14.5	-	ns
t <sub>r</sub>	Rise Time		-	20.2	-	
t <sub>d(off)</sub>	Turn-off Delay Time		-	93	-	
t <sub>f</sub>	Fall Time		-	161	-	
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> = -15A, dI <sub>F</sub> /dt = 100A/μs	-	28	-	ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge		-	25.7	-	nC
V <sub>S(D)</sub>	Diode Forward Voltage <sup>4</sup>	I <sub>S</sub> = -1A, V <sub>GS</sub> = 0V	-	-	-1.2	V
I <sub>S</sub>	Continuous Source Current	T <sub>C</sub> =25°C	-	-	-65	A

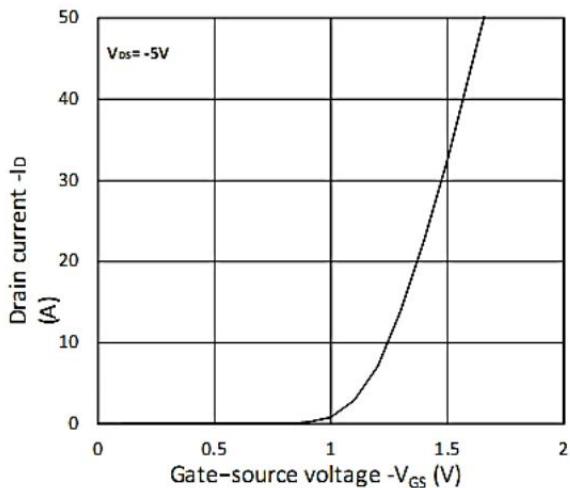
**Note :**

- 1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width  $\leq$  300us , duty cycle  $\leq$  2%
- 3、The power dissipation is limited by 150°C junction temperature
- 4、The EAS data shows Max. rating . The test condition is VDD=-16V,VGS=-10V,L=0.1mH,IAS=12A
- 5、The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub> , in real applications , should be limited by total power dissipation.

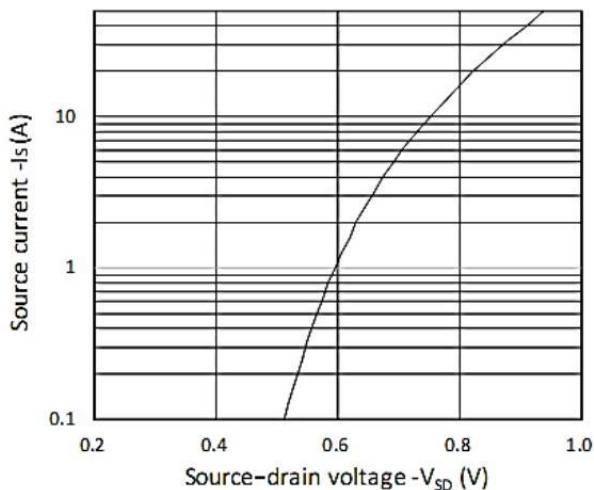
## Typical Characteristics



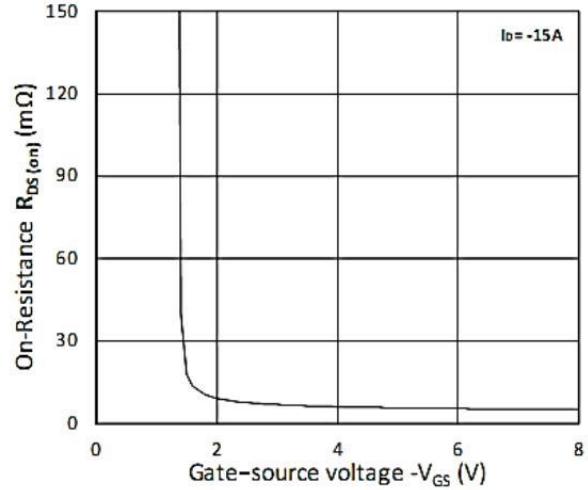
**Figure 1. Output Characteristics**



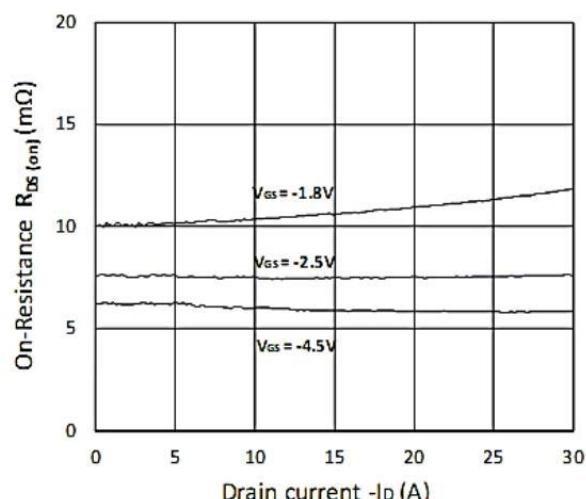
**Figure 2. Transfer Characteristics**



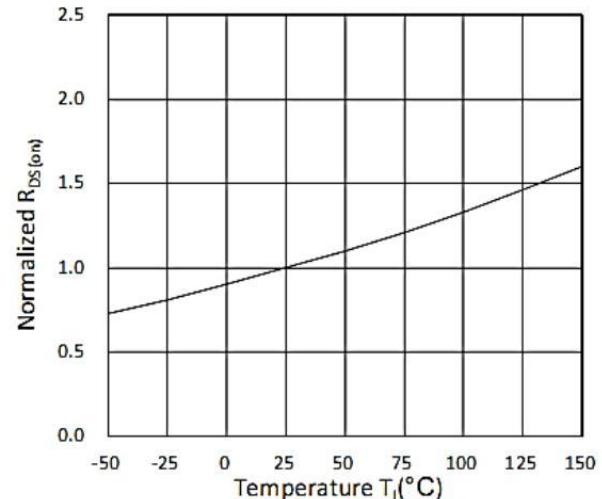
**Figure 3. Forward Characteristics of Reverse**



**Figure 4. RDS(ON) vs. VGS**

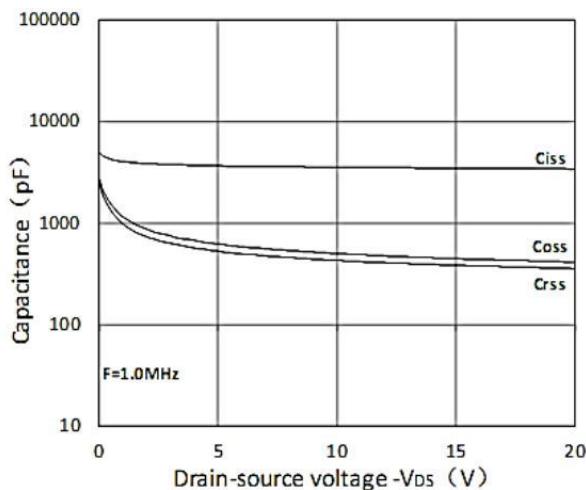


**Figure 5. RDS(ON) vs. ID**

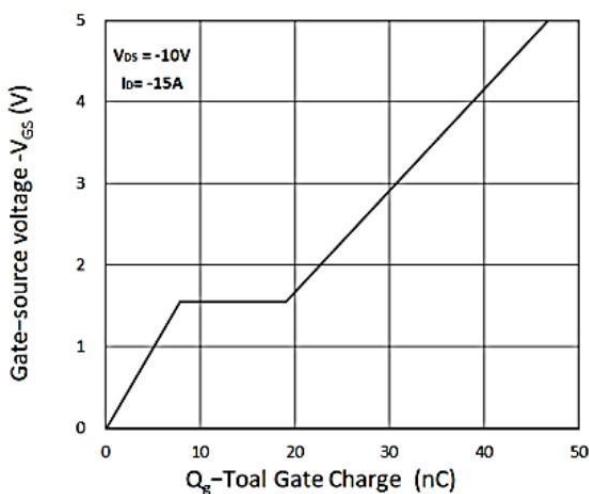


**Figure 6. Normalized R DS(on) vs. Temperature**

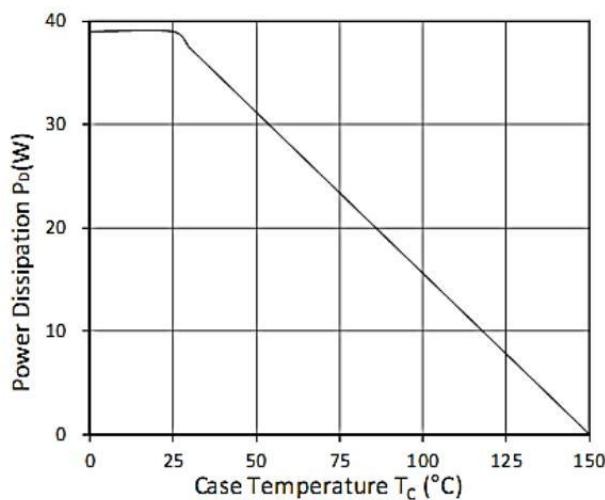
## Typical Characteristics



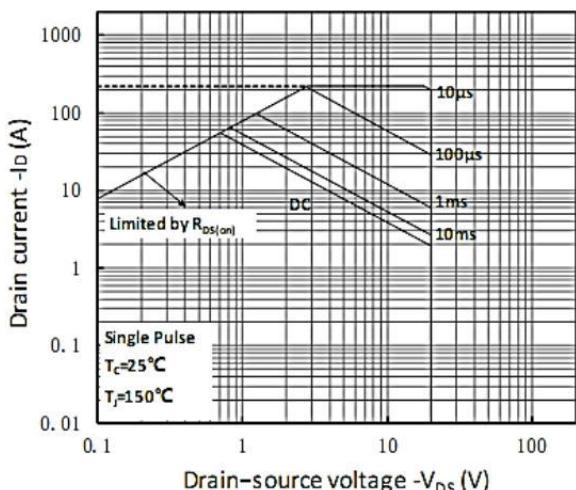
**Figure 7. Capacitance Characteristics**



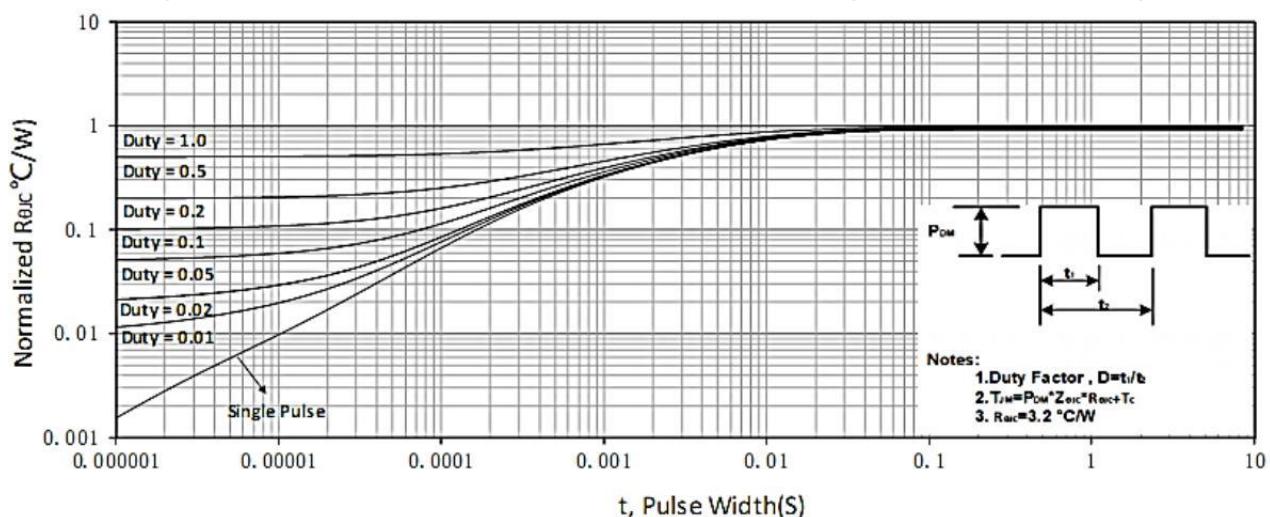
**Figure 8. Gate Charge Characteristics**



**Figure 9. Power Dissipation**

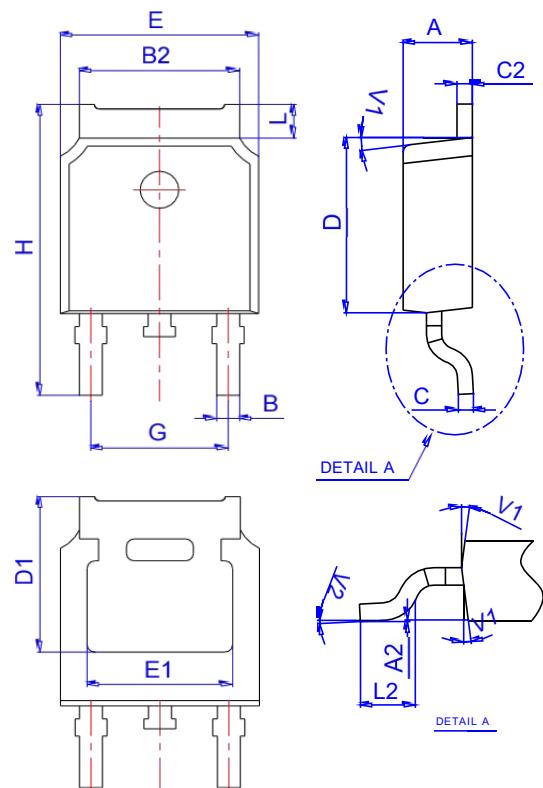


**Figure 10. Safe Operating Area**



**Figure 11 Normalized Maximum Transient Thermal Impedance**

## Package Mechanical Data: TO-252-3L



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

### Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	TO-252-3L		2500